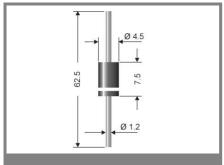
BY 1600...BY 2000



Axial lead diode

Standard silicon rectifier diodes

BY 1600...BY 2000 Forward Current: 3 A

Reverse Voltage: 1600 to 2000 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

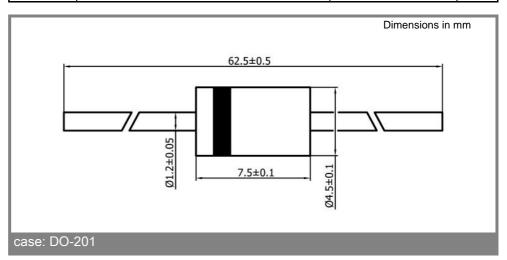
Mechanical Data

- Plastic case DO-201
- Weight approx.: 1 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1700 pieces per ammo
- Valid, if leads are kept at ambient temperature at a distance of 10 mm from
- 2) I_F=3A, T_i=25°C
- 3) T_A = 25 °C

Туре	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V _{RRM} V	V _{RSM} V	I _F = - A I _R = - A I _{RR} = - A t _{rr} ns	V _F ²⁾
BY 1600	1600	1600	-	1,1
BY 1800	1800	1800	-	1,1
BY 2000	2000	2000	-	1,1

Absolute Maximum Ratings Tc = 25°C, unless otherwise specified					
Symbol	Conditions	Values	Units		
I _{FAV}	Max. averaged fwd. current, R-load, T _A = 50 °C ¹⁾	3	Α		
I _{FRM}	Repetitive peak forward current f > 15 Hz ¹⁾	20	Α		
I _{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	80	Α		
i²t	Rating for fusing, t < 10 ms ³⁾	32	A²s		
R _{thA}	Max. thermal resistance junction to ambient 1)	25	K/W		
R _{thT}	Max. thermal resistance junction to terminals 1)	-	K/W		
T _j	Operating junction temperature	-50+150°C	°C		
T _s	Storage temperature	-50+175°C	°C		

Characte	ristics Tc = 25°C	Tc = 25°C, unless otherwise specified		
Symbol	Conditions	Values	Units	
I _R	Maximum leakage current, $T_j = 25 \text{ °C}$; $V_R = V_{RRM}$	<20	μΑ	
	$T_j = {^{\circ}C}; V_R = V_{RRM}$			
С	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF	
Q _{rr}	Reverse recovery charge $(U_R = V; I_F = A; dI_F/dt = A/ms)$	-	μC	
E _{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA; T_j = ^{\circ}C;$ inductive load switched off)	-	mJ	



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